

CLAIM AMENDMENTS

1.-4. (Withdrawn)

5. (Currently Amended) An integrated circuit structure which comprises  
(a) a substrate;

(b) a layer of a first polymeric dielectric material directly on the substrate;

(c) a plurality of spaced apart metal contacts on the layer of the first polymeric dielectric material;

(d) a space between adjacent metal contacts, each space being filled with a second polymeric dielectric material;

(e) a recess in the filled spaces of the layer of the second polymeric dielectric material extending from a level at a top of the metal contacts a part of the distance toward the substrate;

(f) an additional layer of the first polymeric dielectric material directly on at least some of the metal contacts and in the recesses directly on the filled spaces of the second polymeric dielectric material such that there is optionally a gap in at least one of the recesses of the additional layer of first polymeric dielectric material at a side wall of a metal contact;

(g) at least one via extending through the additional layer of the first polymeric dielectric material extending to the top of at least one of the metal contacts and optionally to said gap;

wherein the first dielectric material and the second dielectric material have substantially different etch resistance properties.

6. (Original) The integrated structure of claim 5 wherein the via is filled with at least one metal.

7. (Previously Presented) The structure of claim 5 wherein the first polymeric dielectric material is organic and the second polymeric dielectric material is inorganic.

8.-16. (Withdrawn).